

CMKSH-3DO

SURFACE MOUNT
DUAL OPPOSING SILICON
SCHOTTKY DIODES

ULTRAmTM



SOT-363 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKSH-3DO incorporates two (2) galvanically isolated, Low V_F Silicon Diodes with an opposing Anode/Cathode configuration, in a space saving surface mount package, designed for fast switching applications requiring a low forward voltage drop.

MARKING CODE: KDO

FEATURES:

- Dual Opposing (DO) Schottky Diodes
- Small ULTRAmTM SOT-363 Package
- Galvanically Isolated
- Low Forward Voltage (0.58V TYP @ 100mA)

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Peak Repetitive Reverse Voltage
Continuous Forward Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{RRM} 30
 I_F 100
 P_D 250
 T_J, T_{stg} -65 to +150
 Θ_{JA} 500

UNITS

V
mA
mW
 $^\circ\text{C}$
 $^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

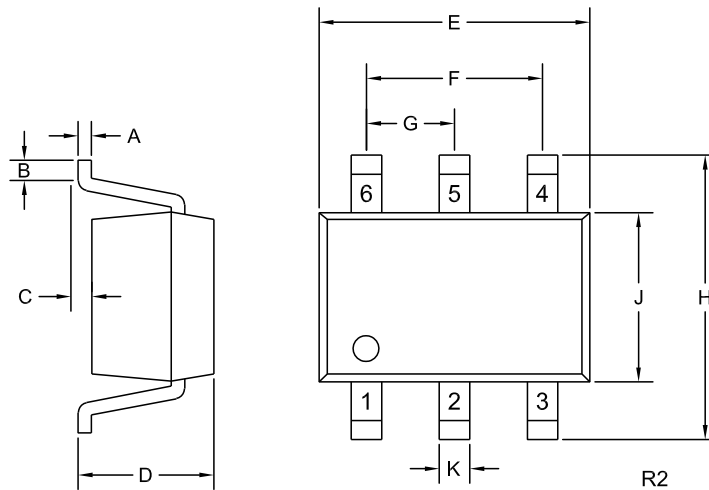
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=25\text{V}$			500	nA
I_R	$V_R=25\text{V}, T_A=100^\circ\text{C}$			100	μA
BV_R	$I_R=100\mu\text{A}$	30			V
V_F	$I_F=2.0\text{mA}$			0.33	V
V_F	$I_F=15\text{mA}$			0.45	V
V_F	$I_F=100\text{mA}$		0.58	1.00	V
C_T	$V_R=0, f=1.0\text{MHz}$		7.0		pF
t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

CMKSH-3DO

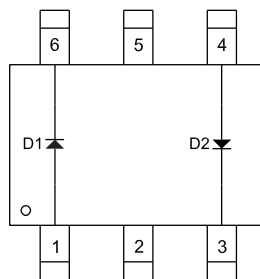
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SOT-363 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) Anode D1
- 2) NC
- 3) Cathode D2
- 4) Anode D2
- 5) NC
- 6) Cathode D1

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SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.010	0.10	0.25
B	0.005	-	0.12	-
C	0.000	0.004	0.00	0.10
D	0.031	0.043	0.80	1.10
E	0.071	0.087	1.80	2.20
F	0.051		1.30	
G	0.026		0.65	
H	0.075	0.091	1.90	2.30
J	0.043	0.055	1.10	1.40
K	0.006	0.012	0.15	0.30

SOT-363 (REV: R2)

R4 (13-January 2010)